

# SAGI RAMA KRISHNAM RAJU ENGINEERING COLLEGE (AUTONOMOUS)

(Approved by AICTE, New Delhi, Affiliated to JNTUK, Kakinada)

Accredited by NAAC with 'A+' Grade

Recognised as Scientific and Industrial Research Organisation SRKR MARG, CHINA AMIRAM, BHIMAVARAM – 534204 W.G.Dt., A.P., INDIA

**Regulation: R23** 

## **ELECTRONICS AND COMMUNICATION ENGINEERING (Minors)**

(Applicable for AIDS, AIML, CIC, CSBS, CSE, CSG, CSIT, CIVIL, IT&ME)

## COURSE STRUCTURE

(With effect from 2023-24 admitted Batch onwards)

Course Code	Course Name	Year/ Sem	Cr	L	Т	P	C.I.E	S.E.E	Total Marks
B23ECM101	Basic Electronics	II-II	3	3	1	0	30	70	100
B23ECM201	Signals & Systems	III-I	3	3	1	0	30	70	100
B23ECM301	Principles Of Communications	III-II	3	3	-1-	0	30	70	100
B23ECM401	Basic VLSI Design	IV-I	3	3	1	0	30	70	100
B23ECM501	*MOOCS-I	II-II to IV-I	3						100
B23ECM601	*MOOCS-II	II-II to IV-I	3				-1-		100
		ГОТАL	18	12	4	0	120	280	600

\*Two MOOCS courses of any **ELECTRONICS AND COMMUNICATION ENGINEERING** related Program Core Courses from NPTEL/SWAYAM with a minimum duration of 12 weeks (3 Credits) courses other than the courses offered need to be taken by prior information to the concern. These courses should be completed between II Year II Semester to IV Year I Semester.

Cour	rse Code	Category	L	Т	P	С	C.I.E.	S.E.E.	Exam
B23I	ECM101	Minors	3	-		3	30	70	3 Hrs
								l	
				BASIC	ELECT	RONIC	S		
			(N	Iinors D	egree Co	ourse in E	ECE)		
Cour	se Objec	ctives:							
1.	Fundan	nental operating	g charact	eristics o	of active	elements s	such as BJT	and Junction	FET.
2.		peration of MC							chanism.
3.	Analyzo characto	e the effect of recristics.	egative	feedback	on ampl	ifier char	acteristics an	d derive the	
4.		nd understand		principl	e of osci	llator circ	uits and perf	orm the analy	ysis of
т.	differen	t oscillator circ	cuits.						
	se Outco	omes: At the en	nd of the	course, S	Students	will be ab	ole to		
S.N				Ou	tcome				Knowledge
0	Illustr	ate the charac	storistics	of DIT	in CE	CP con	figurations	along with	Level
1.	biasing		lensues	OI BJ1	III CE,	CB COI	ingurations	along with	K3
2.	_	ret the Operati	on and t	he charac	eteristics	of JFET.	-		K3
3.	_	n the Operation					c knowledge	e of CMOS	К3
4.		ate the operation	on of fee	dback an	nplifiers.	RING	COLL	EGE	К3
5.	Analy	ze the LC and I	RC oscill	lators.	AU	TONON	lous		К3
					7777 7 4 7	NI C			
	1 1	S 4-1-	- C T		SYLLAF	5US			
	UNIT-I (8 Hrs)  Fundamentals of Transistors:  Bipolar Junction Transistor (BJT) construction & Basic operation, Act Saturation modes of operation, CB, CE configurations, Input and Output ch Transistor as an Amplifier and a Switch, Self and fixed biasing.(without analysis).				characteristics,				
	<del> </del>	2.13 . <b>cc</b>		(DDT)	_				
	Field effect transistors (FET's):  UNIT-II  Junction Field Effect Transistor (JFET) Operation, n-channel JFET, p-ch  (8 Hrs) Pinch-off Voltage, Volt-Ampere characteristics, Advantages of FET  Applications of FET.								
	1	Tetal oxide ser	nicondu	ctor Fiel	ld effect	trancisto	rs (MOSFF	· (2T	
UNIT	T-III C	Construction a	nd Ope Enhanc	eration, ement ar	Classific nd Deple	ation of tion mode	MOSFETS es. Compari	S: N-channe son between	l(NMOS), P-BJT, FET and

		Feedback Amplifiers:					
UNI	T-IV	Feedback principle and concept, types of feedback, classification of amplifiers, feedback					
(8 F	Hrs)	topologies, Characteristics of negative feedback amplifiers, Generalized analysis of					
		feedback amplifiers (without mathematical analysis).					
		Oscillators:					
UNI	IT-V	Oscillator principle, condition for oscillations, types of oscillators, RC- phase shift and					
(8 F	Hrs)	Wien bridge oscillators, Generalized analysis of LC Oscillators, Hartley and Colpitt's					
		oscillators using BJT(without mathematical analysis).					
Text	books						
1.	Elec	tronic Devices and Circuit Theory – Robert L.Boylestad and Lowis Nashelsky, Pearson					
1.	Edit	ion, 2021.					
2.	Elec	tronic devices and circuits by S.Salivahanan and N.Sureshkumar, Tata MCGrawHilledition.					
Refe	rence l	Books:					
1.	Integ	grated Electronics: Analog and Digital circuits and systems by Jacob Millman and Christos					
1.	C.H	alkias, Tata MCGraw Hill edition.					
2.	Elec	tronic Devices and Circuits by Sanjeev Guptha, DhanapatRai publications.					
e-Res	source	s if a later to the second sec					
1.	https	s://books.google.co.in/books?id=Qta8v9hJBMAC&printsec=copyright#v=onepage&q&f=fa					
1.	<u>lse</u>	ENGINEERING COLLEGE					

Estd. 1980

AUTONOMOUS

		Course (		23EC	
		SAGI RAMA KRISHNAM RAJU ENGINEERING COLLEGE (A	.)		R23
		II B.Tech. II Semester MODEL QUESTION PAPER BASIC ELECTRONICS			
Tim	ne: 3 H	(Minors Degree Course in ECE)	Max. M	[anlean	70 M
1 1111	ie: 3 i	Answer Question No.1 compulsorily	viax. IV	tarks:	/U IVI
		Answer Question No.1 compaisority  Answer ONE Question from EACH UNIT			
		Assume suitable data if necessary			
		Assume surcusic data is necessary	10 x 2	= 20 N	
			CO	KL	M
1.	a).	When does a transistor act as a switch?	1	2	2
	b).	What is meant by biasing a transistor?	2	1	2
	c).	Why FET is called as voltage operated device?	2	2	2
	<b>d</b> ).	Comparison between JFET and MOSFET.	3	1	2
	e).	Explain the depletion node of operation in MOSFET?	3	2	2
	f).	Explain PMOSFET	4	1	2
	<b>g</b> ).	List out the various types of feedback topologies.	4	1	2
	h).	Discuss the merits and demerits of negative feedback amplifiers.	5	1	2
	i).	Write down the general applications of oscillators.	5	2	2
	<b>j</b> ).	State the Barkhausen criterion for an oscillator	5	2	2
	-		5 x 10	= 50  N	<u> Marks</u>
		UNIT-1			
2.	a).	Plot the input and output characteristics of transistor in CEconfiguration?	1	2	5
	<b>b</b> ).	Explain different modes of operation of a BJT.	1	3	5
		OR			
3.		Explain the operation of a BJT in self-bias.	1	4	10
-		UNIT-2			
4.	a).	List out the advantages of FET over BJT.	2	3	5
	<b>b</b> ).	Write a brief note on the characteristics of a Junction FET.	2	2	5
		OR			
5.		Explain the construction and working of a n-channel JFET.	2	3	10
		UNIT-3			
6.	a).	Write a brief note on construction and operation of a N-MOSFET.	3	4	5
	<b>b</b> ).	List out the comparisons between BJT, FET and MOSFET.	3	4	5
		OR			
7.		Explain the operation of complementary metal oxide semiconductors.	3	3	10
		UNIT-4			
8.	a).	Explain the classification of amplifiers?	4	3	5
	<b>b</b> ).	Explain voltage series feedback amplifier.	4	3	5
		OR			

9.	Explain current shunt and voltage shunt feedback amplifiers?	4	3	10
	UNIT-5			
10.	Explain the working of Hartley oscillator using BJT	5	3	10
	OR			
11.	Explain the working of RC phase shift oscillator.	5	3	10

CO-COURSE OUTCOME

KL-KNOWLEDGE LEVEL

M-MARKS



Cour	rse Code	e Category	L	T	P	С	C.I.E.	S.E.E.	Exam		
B23I	ECM201	Minors	3			3	30	70	3 Hrs.		
				1	<u> </u>			<u>I</u>			
				SIGNAI	LS AND	SYSTEM	IS				
			(N.	linors D	egree Co	urse in E	CCE)				
Cour	se Obje	ctives:									
1.		o introduce the fundamental concepts and techniques associated with the understanding of gnals and systems.									
2.	To far transfo	niliarize with rms.	techniqu	es suita	ble for	analyzing	continuous	s-time LTI	systems using		
3.	To fam	iliarize with de	velopme	ent of ma	thematic	al skills to	solve prob	lems involvii	ng convolution		
Cour	se Outc	omes: At the en	d of the	course, S	Students	will be ab	le to				
S.N o				Ou	itcome				Knowledge Level		
1.	Apply	the basic conce	epts of si	gnals an	d systems	S			К3		
2.	_	<b>ze</b> the spectral or analysis.	characte	ristics of	Continu	ous Time	aperiodic si	gnals using	K4		
3.	Apply	Lap <mark>lace transf</mark> o	orms for	analyzin	ıg continu	ous time	signals and	systems	К3		
4.	Apply	Z- transforms	for analy	zing disc	crete-time	e signals a	and systems.		К3		
5.	Outlin	e the process o	f sampli	ng and th	ne effects	of under	sampling.	EGE	K2		
		Estd. 1980			AU	TONON	1005				
				Š	SYLLAB	SUS					
	]	introduction to	Contin	uous –T	ime and	Discrete -	-Time Sign	als			
UNI	IT-I	Continuous–Tin	ne & Di	screte-T	ime signa	als, Signa	l Energy an	d Power, Pe	riodic Signals		
(8 H	Irs)	Even & odd Signals, Continuous-Time complex Exponential and Sinu									
(0 =	I	Discrete-Time complex Exponential and Sinusoidal Signals and their F									
	(	Continuous–Tin	ne and D	iscrete-	<u> Γime Uni</u>	t Impulse	and Unit ste	ep Functions.			
	1	ntroduction to	Contin	uous –T	ime and	Discrete -	–Time Syste	ems			
		Continuous–Tin					•		connections o		
UNI'		Systems, Basic S			•	_					
(8 H		Discrete Time L	•	-				nvolution In	tegral and The		
( -	•	Convolution Su	•		-	-			_		
		Equations, Sing			•		,				
	<u> </u>										
***											
	UNIT-III (8 Hrs)  Continuous time Fourier Transform Introduction, Representation of Aperiodic signals, Continuous time Fourier Properties of the continuous time Fourier Transform, Systems characters constant coefficient differential equations.										

		Laplace Transform					
UNI	Γ-IV	Introduction, The Laplace Transform, Region of convergence for Laplace Transforms, The					
(8 H	(rs)	Inverse Laplace Transform, Properties of Laplace Transforms, The initial and Final value					
		theorems.					
		Sampling Theorem and Z-Transform					
		Introduction to Sampling Theorem, Statement of Sampling Theorem for Low pass signals					
UNI	T-V	(Theorem Proof for Low Pass signals only), Discussion on Critical sampling,					
(10 F)	Hrs)	Oversampling and Under sampling (aliasing), The Z-Transform, The Inverse ZTransform,					
		Properties of Z-Transform, Initial and Final Value theorems, Some common Z-transform					
		pairs.					
Textb	ooks:						
1.	Signa	als Systems and Communication-B. P. Lathi, BS Publication.					
2.	Signa	als and Systems- Alan V. Oppenheim, Alan S. Willsky and Ian T. Young, PHI, 2ndEdn.					
Refer	ence l	Books:					
1.	Signa	als and Systems – P.RamakrishnaRao, TMH.					
2.	Signa	als and Systems- A.AnandKumar,PHI					
e-Res	ource						
1.	https	://ocw.mit.edu/resources/res-6-007-signals-and-systems-spring-2011/videolectures/					
2.	https	://swayam.gov.in/nd1_noc20_ee06/preview					
		Estd, 1980 AUTONOMOUS					

		Course Co	de: B	<b>23EC</b> I	M201
		SAGI RAMA KRISHNAM RAJU ENGINEERING COLLEGE (A)			R23
		III B. Tech I Semester MODEL QUESTION PAPER			
		SIGNALS AND SYSTEMS			
7D*	2.1	(Minors Degree Course in ECE)	<b>1 1 1 1</b>	r. 1	70 N /
Tim	e: 3 H		lax. M	larks:	/U M
		Answer Question No.1 compulsorily Answer ONE Question from EACH UNIT			
		Assume suitable data if necessary			
		•	10 x 2	= 20 N	Iarks
			CO	KL	M
1.	a).	Explain how a power signal is different from an energy signal with an example	1	2	2
	<b>b</b> ).	What are the properties to be satisfied by the LTI system?	1	2	2
	c).	Give expressions for convolution integral and convolution sum?	2	2	2
	<b>d</b> ).	Evaluate even and odd components of $x(t) = \sin(t)\cos(t) - \sin(t)$	2	2	2
	e).	State the differentiation in time domain property of the continuous-time Fourier Transform.	3	2	2
	f).	Let x(t)=j/πt, Evaluate it's Fourier Transform	3	3	2
	<b>g</b> ).	What is the relation between Laplace transform and Fourier transform?	4	2	2
	h).	An LTI system h(t) is stable, Discuss ROC of system function H(s).	4	2	2
	i).	State the Nyquist criterion for sampling continuous-time signals.	5	2	2
	<b>j</b> ).	What is the time shifting property of Z transform?	5	2	2
		:	5 x 10	= <b>50</b> N	Iarks
		UNIT-1			
2.	a).	Explain all classification of signals with examples for each category.	1	3	5
	b).	Determine the power of the following signals. $1)x(t) = 5\cos (50t)$ $2)y(t) = e^{j20t}$	1	3	5
		OR			
3.	a).	Prove the energy of the power signal is infinite over infinite time.	1	3	5
	b).	Find weather the below signals are periodic or not, if periodic find periodicity also.  1) $x(t) = \cos(0.1\pi n)$ 2) $y(t) = \cos(20t)$	1	3	5
		UNIT-2			
4.	a).	Determine whether the following systems are time in variant or not. $1)y(t) = x(t^2)$	2	2	5

		2)y(t) = x(2n)			
	<b>b</b> ).	Find the convolution of the following two discrete time sequences	2	2	5
		$x(n)=\{1, 2, 5, 4\}$ and $y(n)=\{6, 2, 4, 3\}$ .			3
		OR			
	a).	Find the convolution of the following two signals.	2	3	5
		$x(t) = e^{at}u(t) \& h(t) = u(t)$	_		
5.	<b>b</b> ).	Explain all classification of systems with examples for each category.	2	3	5
		UNIT-3			
6.	a).	State and derive time shifting and time scaling Properties of Fourier Transform.	3	3	5
	b).	Find the Fourier transform of the following			
		$1. e^{at} u(t)$			
		2. $\cos(3t) u(t)$	3	3	5
		OR			
7.	a).	Find the inverse Fourier transform of $X(jw) = 1/(1+jw)^2$	3	3	5
	<b>b</b> ).	State and prove the differentiation in the frequency domain property of CTFT	3	3	5
		UNIT-4			
8.	a).	Find the Laplace Transform of $x(t) = te^{-at}u(t)$	4	3	5
	<b>b</b> ).	State and prove any two properties of the Laplace Transform.	4	3	5
		OR			
9.	a).	Compute the initial and final values for $X(s) = \frac{2s+5}{s(s+3)(s+4)}$	4	3	5
	<b>b</b> ).	Find the inverse Laplace Transform of $X(s) = \frac{2s}{(s-1)(s+4)}$ ,		2	_
		if ROC is Re{s}>1 & Re{s}<-4	4	3	5
		UNIT-5			
10.	a).	Find the inverse Z – Transform of $X(z) = \frac{z(z-1)}{(z+1)(z+2)}$			
			5	3	5
		with $ROC z  > 2$			
	<b>b</b> ).	State the Nyquist sampling theorem and discuss effects of under sampling,	5	3	5
		OR			
11.	a).	List out the properties of ROC of Z – Transform.	5	3	5
	<b>b</b> ).	Find the Z – Transform of the signal $\left(\frac{1}{2}\right)^n u(n)$	5	3	5
	~~~	COLIDSE OUTCOME - KI KNOWI EDGE LEVEL - M-M	ADV	~	

# CO-COURSE OUTCOME

KL-KNOWLEDGE LEVEL

**M-MARKS** 

Cour	se Code	Category	L	T	P	C	C.I.E.	S.E.E.	Exam	
B23F	ECM301	Minors	3			3	30	70	3 Hrs.	
			PRINC	CIPLES	OF CON	<b>IMUNIC</b>	ATIONS			
			(N.	Iinors D	egree Co	ourse in E	ECE)			
Cour		ives: Students								
1.	analog m	iliarize with the fundamental concepts of communication systems and various techniques of og modulation and demodulation of signals.								
2.		e the element es of generation	•	-	_		•	and familiar	rize with basic	
3.	Introduc	e the elementa	ary conce	epts of di	gital rep	resentatio	n of analog s	signals.		
Cour	se Outcor	mes: At the en	nd of the	course,	Students	will be ab	ole to			
S.No					itcome				Knowledge Level	
1.		<b>ntiate</b> variou e the performa	_						K4	
2.		<b>ntiate</b> variou the <mark>perform</mark> a	. ·	-				chemes and	K4	
3.		r <mark>ize</mark> the sar llation technic		and diff	erentiate	various	Pulse modu	ulation and	K2	
4.	Aware	of basic conce	epts of d	igital rep	resentati	on of anal	og signals.	EGE	K2	
5.	Familia	rize the conc	epts of d	igital mo	odulation	technique	es. U5		K2	
					SYLLAI					
	UNIT-I (10Hrs)  AMPLITUDE MODULATION: Introduction, Frequency Translation, Modulation, Switching Modulator, Envelope Detector, Double Side Band- Carrier Modulation, Ring Modulator, Coherent Detection, Quadrature Modulation, SSB Modulation, VSB Modulation, Frequency-Division Multiplex						nd-Suppressed re Amplitude			
	Wide Band FM, Transmission Bandwidth of FM Signals, Generation of Demodulation of FM Signals, Phase-Locked Loop FM demodulator. If Effect, Pre-Emphasis and De-Emphasis in FM.				FM Signals,					
PULSE MODULATION: Introduction, why digitize analog sources? The Sampling Process, Pulse Amplitude Modulation. Time Division Multiplexing, Modulation, Pulse-Position Modulation, Generation and Detection of PWN waves.							g, Pulse width			

UNIT	Ouantization error Pulse Code Modulation Companding TI Digital system Differential I						
(08 H	Pulse Code Modulation, Delta Modulation.						
UNIT	DIGITAL MODULATION AND TRANSMISSION: Binary Phase-Shift Keying,						
(08 H	Differential Phase-Shift Keying Differentially Encoded PSK (DEPSK). Quadrature Phase I						
(00 1)	Shift Keying (QPSK), M-ary PSK, Binary Frequency Shift-Keying.						
	•						
Textb	ooks:						
1.	Principles of Communication Systems, H.Taub&D.L.Schilling, TMH, 2011						
2.	Communication Systems, Simon Haykins & Moher, 5th Edition, John Willey, India Pvt. Ltd,						
<b></b> .	2010, ISBN 978 – 81 – 265 – 2151 – 7.						
Refer	ence Books:						
1.	Modern Digital and Analog Communication Systems, B. P. Lathi, Oxford University Press., 4 <sup>th</sup>						
1.	edition.						
2.	An Introduction to Analog and Digital Communication, Simon Haykins, John Wiley India Pvt.						
	Ltd., 2008, ISBN 978-81-265-3653-5.						
3.	Communication Systems, Harold P.E, Stern Samy and A.Mahmond, Pearson Edition, 2004.						
4.	Communication Systems: Analog and Digital, R.P.Singh and S.Sapre: TMH 2 <sup>nd</sup> edition, 2007.						
e-Reso	ources						
1.	https://nptel.ac.in/courses/117/105/117105143/						
2.	https://nptel.ac.in/courses/117/101/117101051/						
3.	https://www.tutorialspoint.com/analog_communication/index.htm						
4.	https://www.tutorialspoint.com/digital_communication/index.htm						

		Course Co	de: B	23EC	M301
		SAGI RAMA KRISHNAM RAJU ENGINEERING COLLEGE (A)			R23
		III B.Tech II Semester MODEL QUESTION PAPER			
		PRINCIPLES OF COMMUNICATIONS			
		(Minors Degree Course in ECE)			
Tim	ne: 3 H	Irs. N	Iax. M	larks:	<b>70 M</b>
		Answer Question No.1 compulsorily			
		Answer ONE Question from EACH UNIT			
		Assume suitable data if necessary			
			10 x 2		
			CO	KL	M
1.	a).	What is frequency translation, and why is it used in communication systems?	1	2	2
	<b>b</b> ).	Explain the purpose of an envelope detector in amplitude modulation.	1	3	2
	c).	Differentiate between Narrowband FM and Wideband FM.	2	2	2
	<b>d</b> ).	What is the function of pre-emphasis in FM systems?	2	3	2
	e).	What is pulse amplitude modulation (PAM)?	3	2	2
	<b>f).</b>	How does pulse-width modulation (PWM) differ from pulse-position modulation (PPM)?	3	3	2
	<b>g</b> ).	What is quantization error in digital communication?	4	2	2
	h).	Define differential pulse code modulation (DPCM).	4	2	2
	i).	What is binary phase-shift keying (BPSK)?	5	2	2
	<b>j</b> ).	What is the role of frequency-shift keying (FSK) in digital communication?	5	2	2
		ENGINEERING COLLEGE			
			5 x 10	= 50 N	<u>Iarks</u>
		Estd. 1980 UNIT-1 UTONOMOUS			
2.	a).	Explain the working principles of amplitude modulation (AM) with suitable diagrams?	1	3	5
	<b>b</b> ).	Explain generation of DSB-SC Signal	1	3	5
3.	<b>a</b> ).	Explain about envelope detection, and its applications	1	3	4
	<b>b</b> ).	Compare and contrast double sideband (DSB), single sideband (SSB), and vestigial sideband (VSB) modulation techniques.	1	3	6
		TINTER A			
4		UNIT-2	_	_	_
4.	a).	Describe the generation and demodulation of FM signals	2	3	5
	<b>b</b> ).	Discuss narrowband and wideband FM	2	3	5
		OR			-
<u></u>	2)	Explain the EM threshold effect	2	3	1
5.	a).	Explain the FM threshold effect.  Discuss the importance of PLL in FM demodulator.			4
	<b>b</b> ).	Discuss the importance of PLL in FM demodulator	2	3	6
	->	UNIT-3			
6.	a).	Why is digitization of analog sources necessary? Explain pulse amplitude modulation (PAM).	3	3	5
	<b>b</b> ).	Discuss time-division multiplexing (TDM) and its significance in pulse	3	3	5

		modulation systems.			
		OR			
7.		Explain how pulse width modulation (PWM) and pulse position modulation (PPM) signals are generated and detected.	3	3	10
		UNIT-4			
8.	a).	Explain pulse code modulation (PCM).	4	3	6
	<b>b</b> ).	Explain delta modulation and highlight its advantages and limitations compared to PCM.	4	3	4
		OR			
9.	a).	Explain the quantization process, including the concept of quantization error.	4	3	5
	<b>b</b> ).	Describe differential pulse code modulation (DPCM).	4	3	5
		UNIT-5			
10.	a).	Discuss M-arysignaling techniques, their significance in improving data transmission rates, and the comparison between M-ary PSK and M-ary FSK.	5	3	5
	<b>b</b> ).	Discuss frequency-shift keying (FSK). Discuss their applications and performance in communication systems.	5	3	5
		OR			
11.	a).	Compare and contrast different digital modulation techniques, such as binary phase-shift keying (BPSK), quadrature phase-shift keying (QPSK)	5	3	6
	<b>b</b> ).	Explain and quadrature phase-shift keying (QPSK) in detail. Discuss their signal representation and error performance.	5	3	4

CO-COURSE OUTCOME KL-KNOWLEDGE LEVEL M-MARKS

Cour	se Code	Category	L	T	P	С	C.I.E.	S.E.E.	Exam		
B23E	ECM401	Minors	3			3	30	70	3 Hrs.		
BASIC VLSI DESIGN											
(Minors Degree Course in ECE)											
Cour	ourse Objectives:										
1.	To introduce various fabrication steps of MOS transistors and their electrical properties.								rties.		
2.		ement the stic									
3.	To expla designs.	To explain MOS technology interconnection such as circuits, scaling models, static and dynamic designs.									
4.	To introd	duce Basic FP	GA Arc	hitecture	and testi	ng metho	ds of digital	circuits.			
	se Outco	mes: At the er	nd of the	course, S	Students	will be ab	ole to				
S.N o	Outcome							Knowledge Level			
1.	Unders	tand CMOS f	abrication	on and M	OS trans	istor char	acteristics.		K2		
2.	Draw la	ayout diagram	s using s	tick diag	rams and	d design ru	ıles.		К3		
3.	Analyz	e delay and sc	aling in	MOS cire	cuits.	7 1			K4		
4.	Apply t	est <mark>ability</mark> tech	niques a	nd under	sta <mark>nd</mark> FP	GA archit	tecture.		К3		
5.	Design	static and dyn	amic CN	AOS logi	c circuits	SOING	COLL	ECE	K4		
		***************************************			ALL	TONOS	IALIS				
		Estd. 1980			SYLLAI		1003				
<ul> <li>UNIT-I (10Hrs)</li> <li>UNIT-I (10Hrs)</li> <li>Introduction: Introduction to IC Technology, Fabrication process: CMOS (NMOS PMOS), Ids versus Vds Relationships, Aspects of MOS transistor Threshold Voltage MOS transistor Transconductance, Output Conductance and Figure of Merit. NMOS Inverter, Pull-up to Pull down Ratio for NMOS inverter driven by another NMOS Inverter and through one or more pass transistors, The CMOS Inverter, Latch-up in CMOS circuits</li> <li>UNIT-II MOS and Bi-CMOS Circuit Design Processes: MOS Layers, Stick Diagrams, Design Rules and Layout, General observations on the Design rules, 2μm Double Metal, Double</li> </ul>						chold Voltage, Merit. NMOS MOS Inverter, CMOS circuits.  grams, Design Metal, Double					
(10 Hrs) Poly, CMOS/BiCMOS rules, Layout Diagrams of NAND and NOR gates and CMOS inverter.											
UNI7 (10 I	Γ-III tra Hrs) De	<b>Basic Circuit Concepts:</b> Sheet Resistance, Sheet Resistance concept applied to MOS transistors and Inverters, Area Capacitance of Layers, Standard unit of capacitance, The Delay Unit, Inverter Delays, Propagation Delays. Scaling of MOS Circuits: Scaling models, Scaling factors for device parameters, Limitations of Scaling on substrate doping.									
UNIT (10 I		est and Testa est. FPGA Bas	-	_		•	_	-	d Built-In-Self e.		

UN	IT-V
(10	Hrs)

**Static CMOS Design:** Complementary CMOS and its static properties, Ratioed logic, Pass Transistor logic- Design of logic gates. Dynamic CMOS Design: Basic principles, speed and power dissipation of dynamic logic, Issues in dynamic logic- charge leakage, charge sharing, Static latches and registers- Latches versus registers, The bistability principle.

#### **Textbooks:**

- Essentials of VLSI Circuits and Systems By Kamran Eshraghian, Douglas and A. Pucknell and Sholeh Eshraghian, Prentice-Hall of India Private Limited,2005 Edition. 2. Digital Integrated Circuits, Jan M. Rabaey, Anantha Chandrakasan and Borivoje Nikolic,2nd edition, 2016
- 2. Digital Integrated Circuits, Jan M. Rabaey, Anantha Chandrakasan and Borivoje Nikolic,2nd edition, 2016.

## **Reference Books:**

- FPGA Based System Design Wayne Wolf, Pearson Education, 2004, Technology and Engineering 2. CMOS Digital Integrated Circuits Analysis and Design, Sung-Mo Kang, Yusuf Leblebici, Tata McGraw Hill Education, 2003.
- 2. CMOS Digital Integrated Circuits Analysis and Design, Sung-Mo Kang, Yusuf Leblebici, Tata McGraw Hill Education, 2003.

### e-Resources

1. <a href="https://www.engineersgarage.com/vlsi-technology-an-overview/">https://www.engineersgarage.com/vlsi-technology-an-overview/</a>

Estd. 1980

2. <a href="https://www.tutorialspoint.com/vlsi\_design/vlsi\_design\_digital\_system.html">https://www.tutorialspoint.com/vlsi\_design/vlsi\_design\_digital\_system.html</a>

ENGINEERING COLLEGE
AUTONOMOUS

		Course C	ode: B	23ECI	M401
		SAGI RAMA KRISHNAM RAJU ENGINEERING COLLEGE (A)			R23
		IV B.Tech I Semester MODEL QUESTION PAPER			
		BASIC VLSI DESIGN			
		(Minors Degree Course in ECE)			
Tim	e: 3 E		Iax. M	arks:	70 M
		Answer Question No.1 compulsorily			
		Answer ONE Question from EACH UNIT			
		Assume suitable data if necessary	10 x 2 :	20 1	faulra
			CO	= 20 N KL	M
1.	a).	Give the basic process for IC fabrication	1	2	2
1.	b).	What is Enhancement mode transistor?	1	3	2
	c).	Give the different types of CMOS process?	2	2	2
	d).	Give the various color coding used in stick diagram?	2	1	2
	e).	What do you mean by inverter delay?	3	1	2
	f).	What are the limitations of scaling	3	2	2
	g).	Give some examples of fault models?	4	2	2
	h).	What are the different methods of programming of PALs?	4	1	2
	i).	Discuss ratoned logic?	5	2	2
	j).	compare Static CMOS and Dynamic CMOS logic?	5	1	2
	10.				
		(抗(者) (4-大) (4-\tau)	5 x 10 :	= 50 N	<b>Iarks</b>
		UNIT-1			
2.	a).	Explain the NMOS fabrication steps with neat diagrams.	1	3	6
	<b>b</b> ).	Derive the relation between pull –up tp pull-down ratio for nMOS inverter.	1	3	4
3.	0)	With neat diagrams explain the process of P-well CMOS Inverter.	1	3	6
J.	a). b).	Explain in detail about latch-up in CMOS	1	3	4
	D).	Explain in detail about faten-up in CWOS	1	3	7
		UNIT-2			
4.		Draw the stick diagrams and layouts for (a) CMOS inverter (b) 3 Input NAND and NOR gates using NMOS Technology	2	4	10
		OR			
5.		Sketch λ-based design rules for wires, transistors and contacts.	2	4	10
		UNIT-3			
6.	a).	What is meant by Delay unit? Estimate NMOS inverter pair delays with relevant example.	3	2	5
	<b>b</b> ).	Write a short note on scaling models.	3	2	5
		OR			
7.	a).	Draw scaled NMOS transistor and derive all scaling factors for device parameters. Consider Combined V and D scaling model.	3	3	5
	<b>b</b> ).	Calculate total on resistance of CMOS inverter where ZPU/ZPD=8/1	3	2	5

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		UNIT-4			
8.	a).	Explain about various Scan design techniques.	4	2	5
	<b>b</b> ).	Explain about controllability and observability?	4	2	5
		OR			
9.	a).	Explain the Basic FPGA Architecture.	4	3	5
	<b>b</b> ).	Write various steps to be followed for test mode in Scan Design	4	2	5
		Techniques?	4	4	3
		UNIT-5			
10.	a).	Write a short note on complementary CMOS and its properties	5	3	6
	<b>b</b> ).	Explain Bi-stability principle.	5	2	4
		OR			
11.		Explain charge leakage and charge sharing in dynamic logics.	5	3	10
1			_	~	

CO-COURSE OUTCOME

KL-KNOWLEDGE LEVEL

M-MARKS

